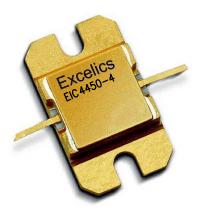


## 4.40-5.00 GHz 4-Watt Internally Matched Power FET

#### **FEATURES**

- 4.40-5.00GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 11.5 dB Power Gain at 1dB Compression
- 37% Power Added Efficiency
- -46 dBc IM3 at PO = 25.5 dBm SCL
- 100% Tested for DC, RF, and R<sub>TH</sub>





#### Caution! ESD sensitive device.

### **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

SYMBOL	PARAMETERS/TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
P <sub>1dB</sub>	Output Power at 1dB Compression $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	35.5	36.5		dBm
G <sub>1dB</sub>	Gain at 1dB Compression $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	10.5	11.5		dB
ΔG	Gain Flatness $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS}$ = 10 V, $I_{DSQ}$ ≈ 1100mA		37		%
Id <sub>1dB</sub>	Drain Current at 1dB Compression f = 4.40-5.00GHz		1200	1500	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10 \text{ MHz } 2\text{-Tone Test}$ ; Pout = 25.5 dBm S.C.L <sup>2</sup> $V_{DS} = 10 \text{ V}$ , $I_{DSQ} \approx 65\% \text{ IDSS}$ f = 5.00GHz	-43	-46		dBc
I <sub>DSS</sub>	Saturated Drain Current $V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}$		2000	2500	mA
V <sub>P</sub>	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 20 \text{ mA}$		-2.5	-4.0	V
R <sub>TH</sub>	Thermal Resistance <sup>3</sup>		5.5	6.0	°C/W

Note: 1. Tested with 100 Ohm gate resistor.

- 2. S.C.L. = Single Carrier Level.
- 3. Overall Rth depends on case mounting.

#### ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	SYMBOLS PARAMETERS		CONTINUOUS <sup>2</sup>	
Vds	Vds Drain-Source Voltage		10V	
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Forward Gate Current	48mA	14mA	
lgr	Reverse Gate Current	-9.6mA	-2.4mA	
Pin	Input Power	36dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Storage Temperature	-65C to +175C	-65C to +175C	
Pt	Pt Total Power Dissipation		25W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

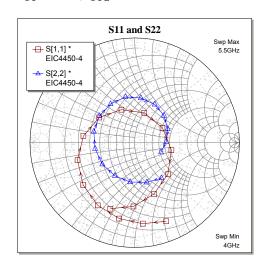


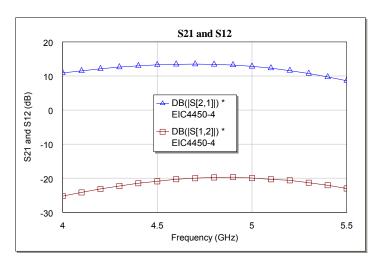


# 4.40-5.00 GHz 4-Watt Internally Matched Power FET

#### PERFORMANCE DATA

Typical S-Parameters (T= 25°C,  $50\Omega$  system, de-embedded to edge of package)  $V_{DS}$  = 10 V,  $I_{DSQ}$   $\approx$  1100mA





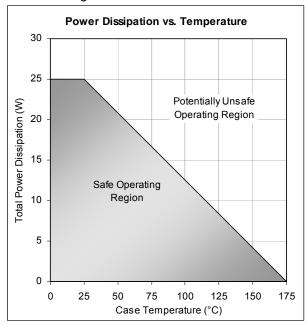
FREQ	S	11	S	S21		S12		22
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
4.00	0.808	-68.190	3.508	99.990	0.055	37.090	0.424	-52.880
4.25	0.713	-110.590	4.141	59.190	0.074	-2.750	0.368	-108.070
4.50	0.570	-163.190	4.620	13.810	0.090	-49.090	0.382	-171.490
4.75	0.383	129.460	4.719	-34.020	0.102	-96.850	0.429	132.270
5.00	0.301	28.000	4.375	-83.660	0.100	-145.990	0.431	82.100
5.25	0.481	-56.790	3.625	-132.810	0.090	165.590	0.364	33.460
5.50	0.671	-110.260	2.699	-177.940	0.071	122.650	0.268	-19.720
5.75	0.795	-149.080	1.929	141.910	0.053	84.390	0.240	-76.080
6.00	0.869	-179.020	1.365	106.080	0.040	51.160	0.290	-122.110
6.25	0.909	156.420	0.965	72.960	0.028	27.210	0.380	-155.490
6.50	0.933	135.760	0.681	42.570	0.020	0.750	0.488	178.060

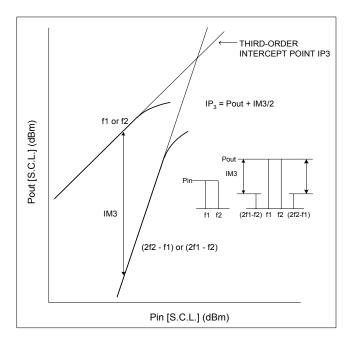




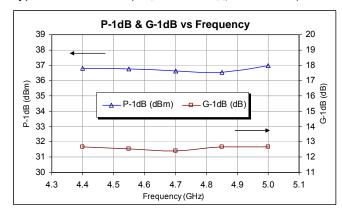
## 4.40-5.00 GHz 4-Watt Internally Matched Power FET

#### Power De-rating Curve and IM3 Definition

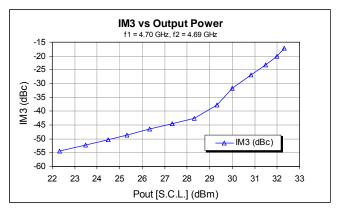




### Typical Power Data ( $V_{DS} = 10 \text{ V}$ , $I_{DSQ} = 1100 \text{ mA}$ )



Typical IM3 Data ( $V_{DS} = 10 \text{ V}$ ,  $I_{DSQ} \approx 65\% \text{ IDSS}$ )



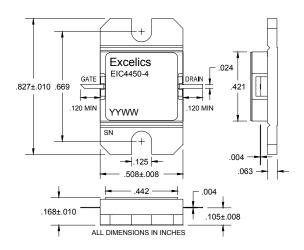


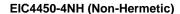
## 4.40-5.00 GHz 4-Watt Internally Matched Power FET

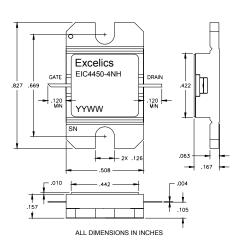
#### **PACKAGES OUTLINE**

Dimensions in inches, Tolerance + .005 unless otherwise specified

#### EIC4450-4 (Hermetic)









Caution! ESD sensitive device.



Caution! ESD sensitive device.

#### ORDERING INFORMATION

Part Number	Packages	Grade <sup>1</sup>	f <sub>Test</sub> (GHz)	P <sub>1dB</sub> (min)	$IM_3 (min)^2$
EIC4450-4	Hermetic	Industrial	4.40-5.00GHz	35.5	-43
EIC4450-4NH	Non-Hermetic	Industrial	4.40-5.00GHz	35.5	-43

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness